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(54) **INTEGRATED CIRCUIT STRUCTURES
HAVING BACKSIDE CAPACITORS**

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(71) Applicant: **Intel Corporation**, Santa Clara, CA
(US)

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(72) Inventors: **Abhishek Anil SHARMA**, Portland,
OR (US); **Tahir GHANI**, Portland, OR
(US); **Anand S. MURTHY**, Portland,
OR (US); **Wilfred GOMES**, Portland,
OR (US); **Pushkar RANADE**, San
Jose, CA (US); **Sagar SUTHRAM**,
Portland, OR (US)

(57)

ABSTRACT

Structures having backside capacitors are described. In an example, an integrated circuit structure includes a front side structure including a device layer having a plurality of select transistors, a plurality of metallization layers above the plurality of select transistors, and a plurality of vias below and coupled to the plurality of select transistors. A backside structure is below the plurality of vias of the device layer. The backside structure includes a memory layer coupled to the plurality of select transistors by the plurality of vias.

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